

NJD35N04G

NPN Darlington Power Transistor

This high voltage power Darlington has been specifically designed for inductive applications such as Electronic Ignition, Switching Regulators and Motor Control.

Features

- Exceptional Safe Operating Area
- High V_{CE} ; High Current Gain
- These are Pb-Free Devices

Benefits

- Reliable Performance at Higher Powers
- Designed for Inductive Loads
- Very Low Current Requirements

Applications

- Internal Combustion Engine Ignition Control
- Switching Regulators
- Motor Controls
- Light Ballast
- Photo Flash

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Sustaining Voltage	V_{CEO}	350	Vdc
Collector-Base Breakdown Voltage	V_{CBO}	700	Vdc
Collector-Emitter Breakdown Voltage	V_{CES}	700	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current	I_C	4.0	Adc
	I_{CM}	8.0	
Base Current	I_B	0.5	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	45	W
		0.36	W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance	$R_{\theta JC}$	2.78	$^\circ\text{C/W}$
	$R_{\theta JA}$	71.4	

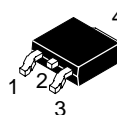


ON Semiconductor®

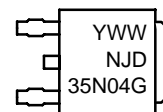
<http://onsemi.com>

**DARLINGTON
POWER TRANSISTORS
4 AMPERES
350 VOLTS
45 WATTS**

MARKING DIAGRAM



DPAK
CASE 369C
STYLE 1



Y = Year
WW = Work Week
NJD35N04 = Device Code
G = Pb-Free Device

ORDERING INFORMATION

Device	Package	Shipping†
NJD35N04G	DPAK (Pb-Free)	75 Units / Rail
NJD35N04T4G	DPAK (Pb-Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NJD35N04G

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Sustaining Voltage ($I_C = 10\text{ mA}$, $L = 10\text{ mH}$)	$V_{CE(sus)}$	350	–	–	Vdc
Collector Cutoff Current ($V_{CE} = 500\text{ V}$) ($I_B = 0$) ($V_{CE} = 500\text{ V}$, $T_C = 125^\circ\text{C}$)	I_{CES}	–	–	50 250	μA_{dc}
Collector Cutoff Current ($V_{CE} = 350\text{ V}$) ($I_B = 0$) ($V_{CE} = 300\text{ V}$, $T_C = 125^\circ\text{C}$)	I_{CEO}	–	–	50 250	μA_{dc}
Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$)	I_{EBO}	–	–	5.0	μA_{dc}

ON CHARACTERISTICS

Collector–Emitter Saturation Voltage ($I_C = 2.0\text{ A}$, $I_B = 20\text{ mA}$) ($I_C = 2.0\text{ A}$, $I_B = 20\text{ mA}$, 125°C)	$V_{CE(sat)}$	–	–	1.5	Vdc
Base–Emitter Saturation Voltage ($I_C = 2.0\text{ A}$, $I_B = 20\text{ mA}$) ($I_C = 2.0\text{ A}$, $I_B = 20\text{ mA}$, 125°C)	$V_{BE(sat)}$	–	–	2.0	Vdc
Base–Emitter On Voltage ($I_C = 2.0\text{ A}$, $V_{CE} = 2.0\text{ V}$) ($I_C = 2.0\text{ A}$, $V_{CE} = 2.0\text{ V}$, 125°C)	$V_{BE(on)}$	–	–	2.0	Vdc
DC Current Gain ($I_C = 2.0\text{ A}$, $V_{CE} = 2.0\text{ V}$) ($I_C = 4.0\text{ A}$, $V_{CE} = 2.0\text{ Vdc}$)	h_{FE}	2000 300	– –	– –	–

DYNAMIC CHARACTERISTICS

Current–Gain – Bandwidth Product ($I_C = 2.0\text{ A}$, $V_{CE} = 10\text{ V}$, $f = 1.0\text{ MHz}$)	f_T	90	–	–	MHz
Output Capacitance ($V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 0.1\text{ MHz}$)	C_{ob}	–	60	–	pF

SWITCHING CHARACTERISTICS

$V_{CC} = 12\text{ V}$, $V_{clamp} = 250\text{ V}$, $L = 4\text{ mH}$ $I_C = 2\text{ A}$, $I_{B1} = 20\text{ mA}$, $I_{B2} = -20\text{ mA}$	t_s t_f	– –	18 0.8	– –	μSec
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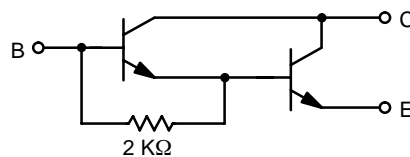


Figure 1. Darlington Circuit Schematic

NJD35N04G

TYPICAL CHARACTERISTICS

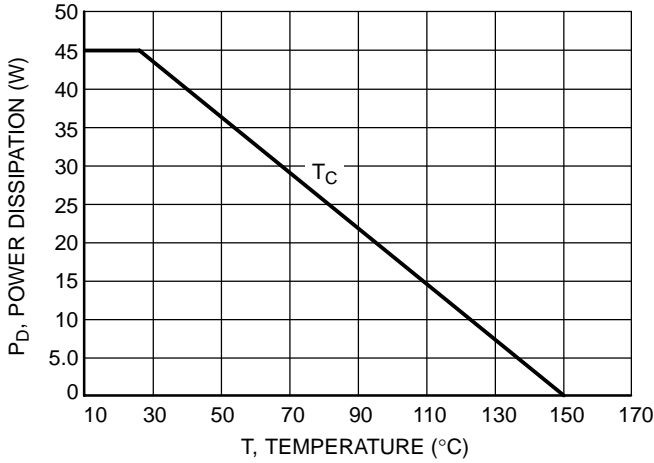


Figure 2. Power Derating

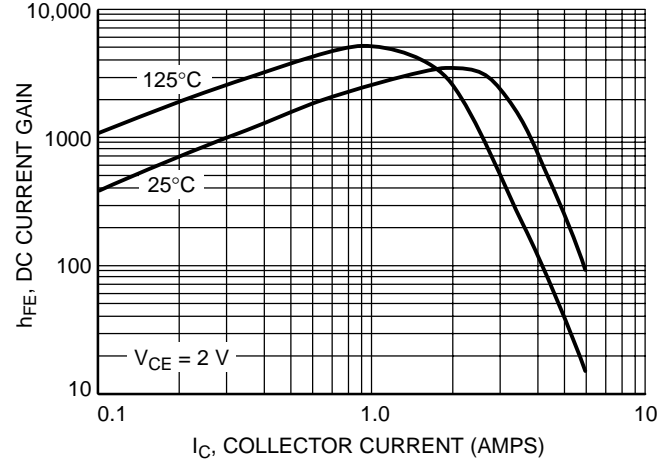


Figure 3. DC Current Gain

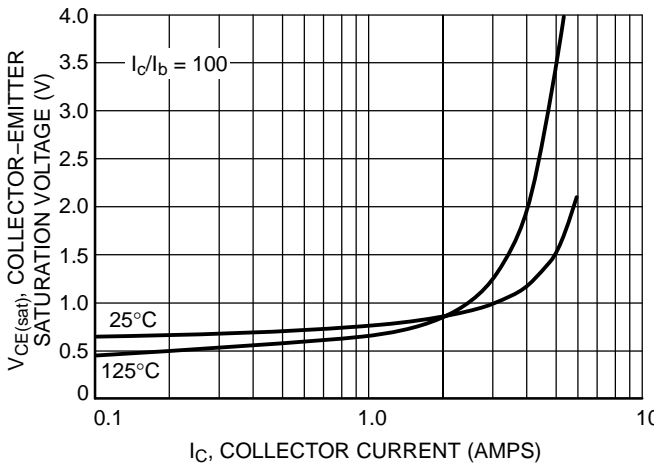


Figure 4. Collector-Emitter Saturation Voltage

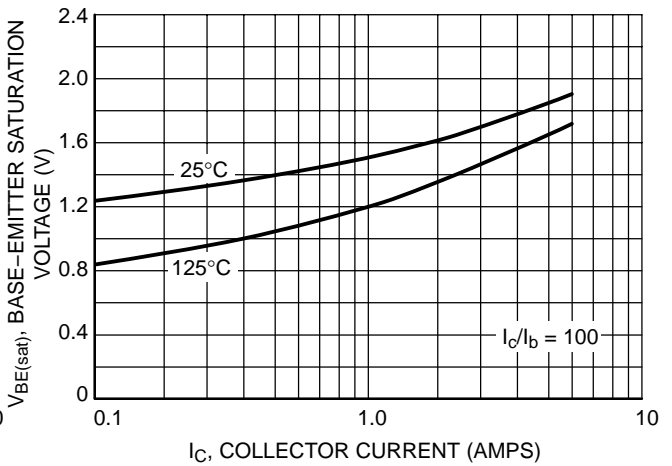


Figure 5. Base-Emitter Saturation Voltage

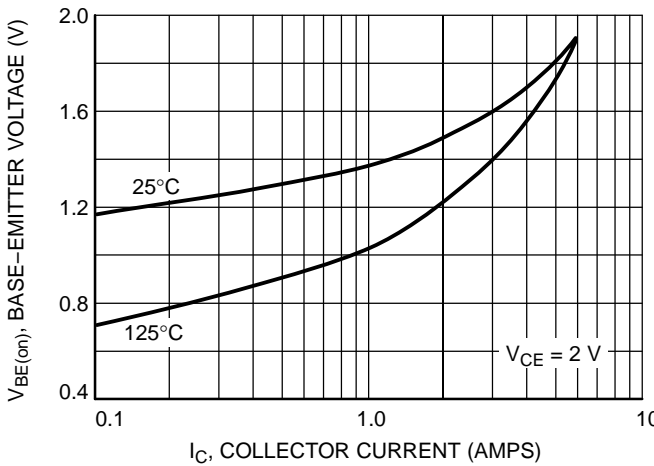


Figure 6. Base-Emitter Voltage

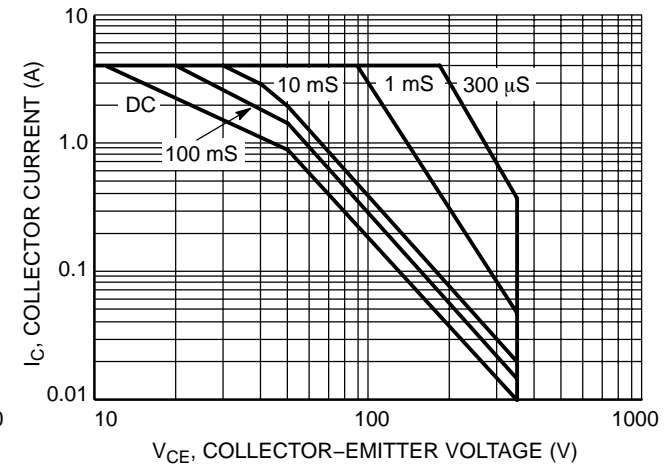
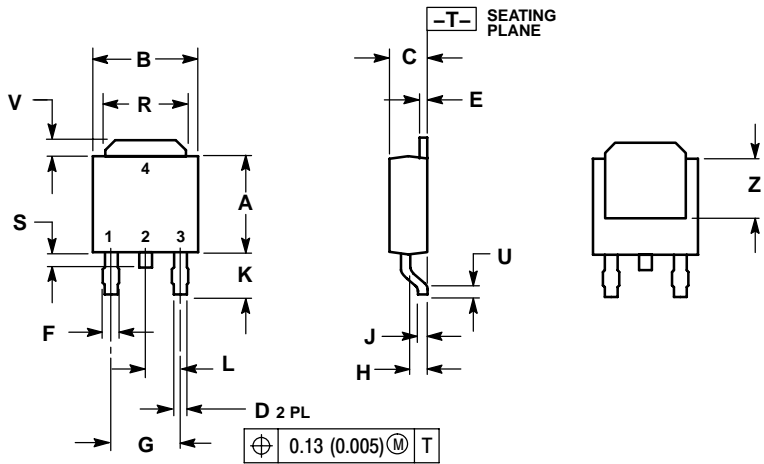


Figure 7. Forward Bias Safe Operating Area (FBSOA)

NJD35N04G

PACKAGE DIMENSIONS

DPAK
CASE 369C-01
ISSUE O



NOTES:

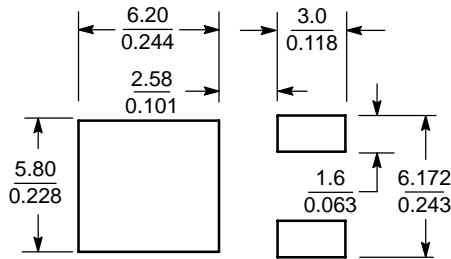
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.180 BSC		4.58 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090 BSC		2.29 BSC	
R	0.180	0.215	4.57	5.45
S	0.025	0.040	0.63	1.01
U	0.020	---	0.51	---
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

STYLE 1:

1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

SOLDERING FOOTPRINT*



SCALE 3:1 (mm/inches)

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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